

# LMX2315/LMX2320/LMX2325 PLLatinum™ Frequency Synthesizer for RF Personal Communications LMX2325 2.5 GHz LMX2320 2.0 GHz LMX2315 1.2 GHz

## General Description

The LMX2315/2320/2325's are high performance frequency synthesizers with integrated prescalers designed for RF operation up to 2.5 GHz. They are fabricated using National's ABiC IV BiCMOS process.

A 64/65 or a 128/129 divide ratio can be selected for the LMX2315 and LMX2320 RF synthesizer at input frequencies of up to 1.2 GHz and 2.0 GHz, while 32/33 and 64/65 divide ratios are available in the 2.5 GHz LMX2325. Using a proprietary digital phase locked loop technique, the LMX2315/2320/2325's linear phase detector characteristics can generate very stable, low noise signals for controlling a local oscillator.

Serial data is transferred into the LMX2320 and the LMX2325 via a three line MICROWIRE™ interface (Data, Enable, Clock). Supply voltage can range from 2.7V to 5.5V. The LMX2315, LMX2320 and the LMX2325 feature very low current consumption, typically 6 mA, 10 mA and 11 mA respectively.

The LMX2315, LMX2320 and the LMX2325 are available in a TSSOP 20-pin surface mount plastic package.

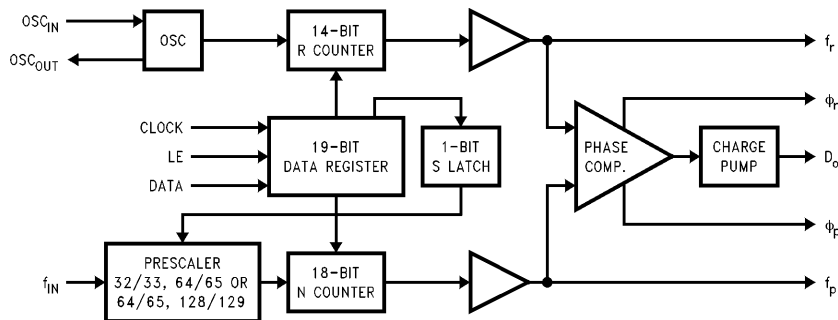
## Features

- RF operation up to 2.5 GHz
- 2.7V to 5.5V operation
- Low current consumption
- Dual modulus prescaler:  
LMX2325 32/33 or 64/65  
LMX2320/LMX2315 64/65 or 128/129
- Internal balanced, low leakage charge pump
- Power down feature for sleep mode:  
 $I_{CC} = 30 \mu A$  (typ) at  $V_{CC} = 3V$
- Small-outline, plastic, surface mount TSSOP, 0.173" wide

## Applications

- Cellular telephone systems (GSM, IS-54, IS-95, (RCR-27))
- Portable wireless communications (DECT, PHS)
- CATV
- Other wireless communication systems

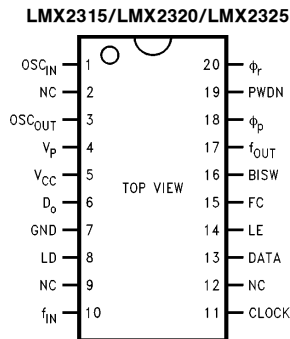
## Block Diagram



TL/W/12339-1

TRI-STATE® is a registered trademark of National Semiconductor Corporation.  
MICROWIRE™ and PLLatinum™ are trademarks of National Semiconductor Corporation.

## Connection Diagrams



TL/W/12339-2

**20-Lead (0.173" Wide) Thin Shrink Small Outline Package (TM)**

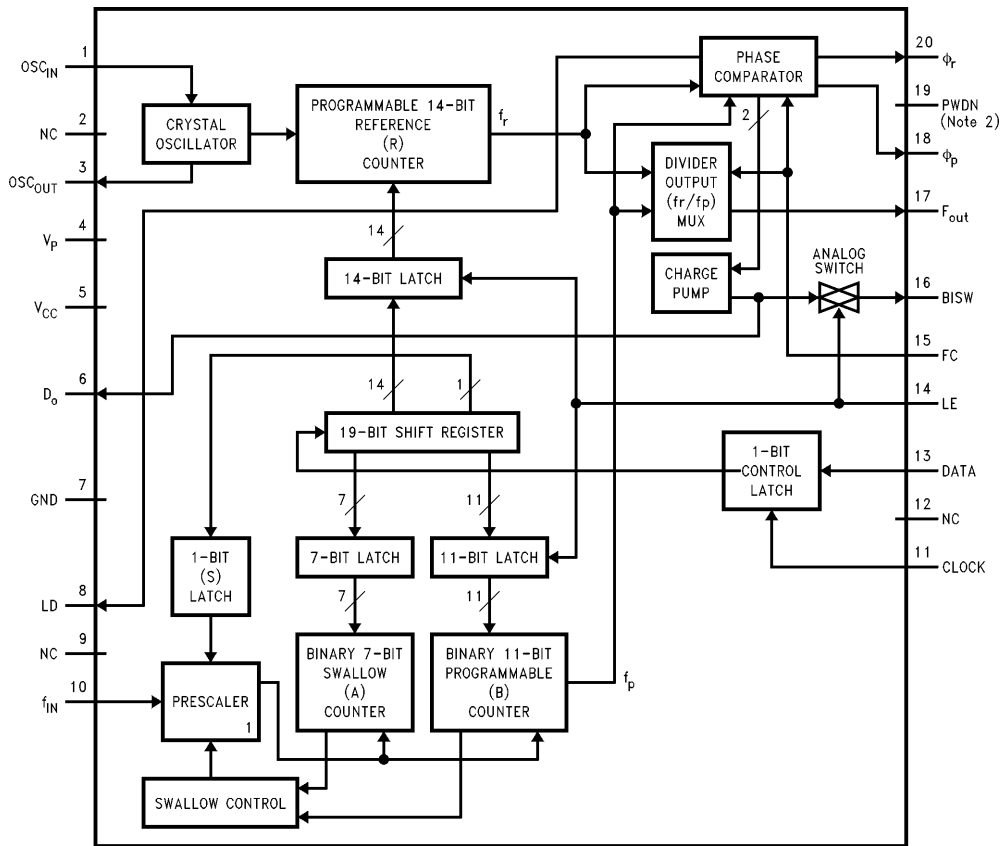
**Order Number LMX2315TM, LMX2315TMX, LMX2325TM, LMX2325TMX, LMX2320TM or LMX2320TMX**

**See NS Package Number MTC20**

## Pin Descriptions

Pin No.	Pin Name	I/O	Description
1	OSC <sub>IN</sub>	I	Oscillator input. A CMOS inverting gate input intended for connection to a crystal resonator for operation as an oscillator. The input has a $V_{CC}/2$ input threshold and can be driven from an external CMOS or TTL logic gate. May also be used as a buffer for an externally provided reference oscillator.
3	OSC <sub>OUT</sub>	O	Oscillator output.
4	V <sub>P</sub>		Power supply for charge pump. Must be $\geq V_{CC}$ .
5	V <sub>CC</sub>		Power supply voltage input. Input may range from 2.7V to 5.5V. Bypass capacitors should be placed as close as possible to this pin and be connected directly to the ground plane.
6	D <sub>o</sub>	O	Internal charge pump output. For connection to a loop filter for driving the input of an external VCO.
7	GND		Ground.
8	LD	O	Lock detect. Output provided to indicate when the VCO frequency is in "lock". When the loop is locked, the pin's output is HIGH with narrow low pulses.
10	f <sub>IN</sub>	I	Prescaler input. Small signal input from the VCO.
11	CLOCK	I	High impedance CMOS Clock input. Data is clocked in on the rising edge, into the various counters and registers.
13	DATA	I	Binary serial data input. Data entered MSB first. LSB is control bit. High impedance CMOS input.
14	LE	I	Load enable input (with internal pull-up resistor). When LE transitions HIGH, data stored in the shift registers is loaded into the appropriate latch (control bit dependent). Clock must be low when LE toggles high or low. See Serial Data Input Timing Diagram.
15	FC	I	Phase control select (with internal pull-up resistor). When FC is LOW, the polarity of the phase comparator and charge pump combination is reversed.
16	BISW	O	Analog switch output. When LE is HIGH, the analog switch is ON, routing the internal charge pump output through BISW (as well as through D <sub>o</sub> ).
17	f <sub>OUT</sub>	O	Monitor pin of phase comparator input. CMOS output.
18	φ <sub>p</sub>	O	Output for external charge pump. φ <sub>p</sub> is an open drain N-channel transistor and requires a pull-up resistor.
19	PWDN	I	Power Down (with internal pull-up resistor). PWDN = HIGH for normal operation. PWDN = LOW for power saving. Power down function is gated by the return of the charge pump to a TRI-STATE® condition.
20	φ <sub>r</sub>	O	Output for external charge pump. φ <sub>r</sub> is a CMOS logic output.
2,9,12	NC		No connect.

## Functional Block Diagram



**Note 1:** The prescaler for the LMX2315 and LMX2320 is either 64/65 or 128/129, while the prescaler for the LMX2325 is 32/33 or 64/65.

**Note 2:** The power down function is gated by the charge pump to prevent unwanted frequency jumps. Once the power down pin is brought low the part will go into power down mode when the charge pump reaches a TRI-STATE condition.

## Absolute Maximum Ratings (Notes 1, 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Power Supply Voltage  
 $V_{CC}$   $-0.3V$  to  $+6.5V$   
 $V_P$   $-0.3V$  to  $+6.5V$

Voltage on Any Pin  
with GND =  $0V$  ( $V_I$ )  $-0.3V$  to  $+6.5V$

Storage Temperature Range ( $T_S$ )  $-65^{\circ}C$  to  $+150^{\circ}C$

Lead Temperature ( $T_L$ ) (solder, 4 sec.)  $+260^{\circ}C$

## Recommended Operating Conditions

Power Supply Voltage  
 $V_{CC}$   $2.7V$  to  $5.5V$   
 $V_P$   $V_{CC}$  to  $+5.5V$

Operating Temperature ( $T_A$ )  $-40^{\circ}C$  to  $+85^{\circ}C$

**Note 1:** Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but do not guarantee specific performance limits. For guaranteed specifications and test conditions, see the Electrical Characteristics. The guaranteed specifications apply only for the test conditions listed.

**Note 2:** This device is a high performance RF integrated circuit with an ESD rating  $< 2$  kV and is ESD sensitive. Handling and assembly of this device should be done at ESD workstations.

## Electrical Characteristics

LMX2325 and LMX2320  $V_{CC} = V_P = 3.0V$ ; LMX2315  $V_{CC} = V_P = 5.0V$ ;  $-40^{\circ}C < T_A < 85^{\circ}C$ , except as specified

Symbol	Parameter		Conditions	Min	Typ	Max	Units
$I_{CC}$	Power Supply Current	LMX2315	$V_{CC} = 3.0V$		6.0	8.0	mA
			$V_{CC} = 5.0V$		6.5	8.5	mA
		LMX2320	$V_{CC} = 3.0V$		10	13.5	mA
		LMX2325	$V_{CC} = 3.0V$		11	15	mA
$I_{CC-PWDN}$	Power Down Current		$V_{CC} = 3.0V$		30	180	$\mu A$
			$V_{CC} = 5.0V$		60	350	$\mu A$
$f_{IN}$	Maximum Operating Frequency	LMX2315		1.2			GHz
		LMX2320		2.0			
		LMX2325		2.5			
$f_{OSC}$	Oscillator Frequency			5		20	MHz
			No Load on $OSC_{out}$	5		40	MHz
$f_{\phi}$	Phase Detector Frequency			10			MHz
$Pf_{IN}$	Input Sensitivity		$V_{CC} = 2.7V$ to $3.3V$	-15		+6	dBm
			$V_{CC} = 3.3V$ to $5.5V$	-10		+6	
$V_{OSC}$	Oscillator Sensitivity		$OSC_{IN}$	0.5			V <sub>PP</sub>
$V_{IH}$	High-Level Input Voltage		*	$0.7 V_{CC}$			V
$V_{IL}$	Low-Level Input Voltage		*			$0.3 V_{CC}$	V
$I_{IH}$	High-Level Input Current (Clock, Data)		$V_{IH} = V_{CC} = 5.5V$	-1.0		1.0	$\mu A$
$I_{IL}$	Low-Level Input Current (Clock, Data)		$V_{IL} = 0V$ , $V_{CC} = 5.5V$	-1.0		1.0	$\mu A$
$I_{IH}$	Oscillator Input Current		$V_{IH} = V_{CC} = 5.5V$			100	$\mu A$
			$V_{IL} = 0V$ , $V_{CC} = 5.5V$	-100			$\mu A$
$I_{IH}$	High-Level Input Current (LE, FC)		$V_{IH} = V_{CC} = 5.5V$	-1.0		1.0	$\mu A$
$I_{IL}$	Low-Level Input Current (LE, FC)		$V_{IL} = 0V$ , $V_{CC} = 5.5V$	-100		1.0	$\mu A$

\*Except  $f_{IN}$  and  $OSC_{IN}$

## Electrical Characteristics

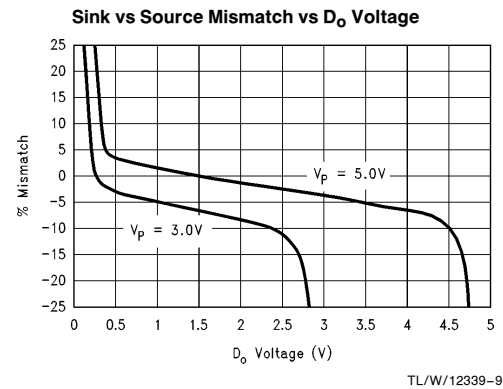
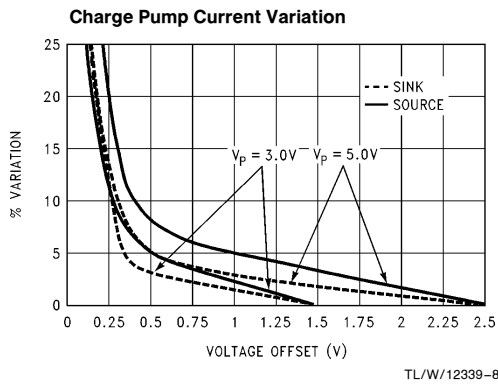
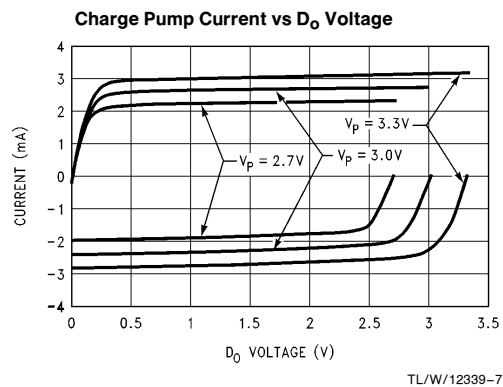
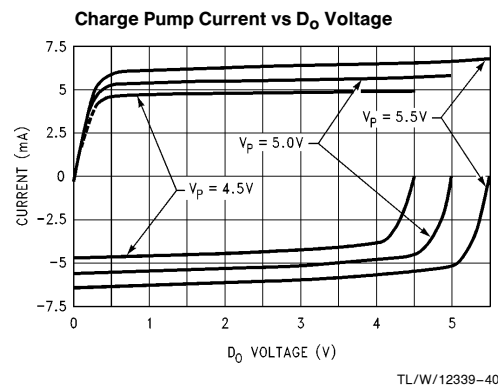
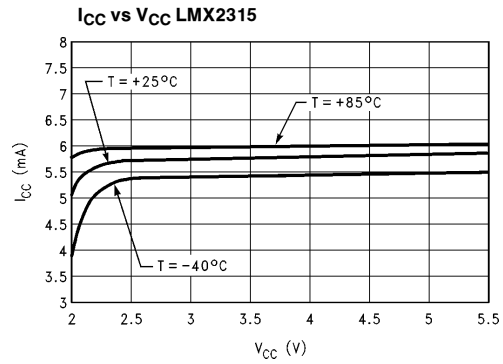
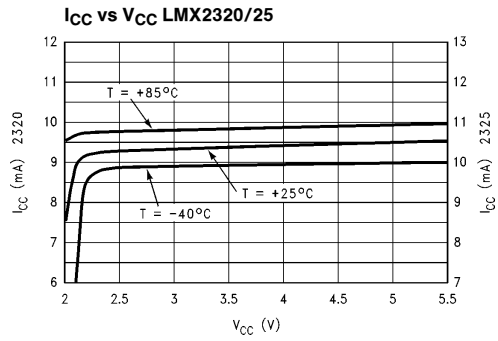
LMX2325 and LMX2320  $V_{CC} = V_P = 3.0V$ ; LMX2315  $V_{CC} = V_P = 5.0V$ ;  $-40^{\circ}C < T_A < 85^{\circ}C$ , except as specified (Continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
$I_{D_O\text{-source}}$	Charge Pump Output Current	$V_{CC} = V_P = 3.0V, V_{D_O} = V_P/2$		-2.5		mA
$I_{D_O\text{-sink}}$		$V_{CC} = V_P = 3.0V, V_{D_O} = V_P/2$		2.5		mA
$I_{D_O\text{-source}}$	Charge Pump Output Current	$V_{CC} = V_P = 5.0V, V_{D_O} = V_P/2$		-5.0		mA
$I_{D_O\text{-sink}}$		$V_{CC} = V_P = 5.0V, V_{D_O} = V_P/2$		5.0		mA
$I_{D_O\text{-Tri}}$	Charge Pump TRI-STATE® Current	$0.5V \leq V_{D_O} \leq V_P - 0.5V$ $T = 85^{\circ}C$	-2.5		2.5	nA
$I_{D_O}$ vs $V_{D_O}$	Charge Pump Output Current Magnitude Variation vs Voltage (Note 1)	$0.5V \leq V_{D_O} \leq V_P - 0.5V$ $T = 25^{\circ}C$			15	%
$I_{D_O\text{-sink}}$ vs $I_{D_O\text{-source}}$	Charge Pump Output Current Sink vs Source Mismatch (Note 2)	$V_{D_O} = V_P/2$ $T = 25^{\circ}C$			10	%
$I_{D_O}$ vs $T$	Charge Pump Output Current Magnitude Variation vs Temperature (Note 3)	$-40^{\circ}C < T < 85^{\circ}C$ $V_{D_O} = V_P/2$		10		%
$V_{OH}$	High-Level Output Voltage	$I_{OH} = -1.0 \text{ mA}^{**}$	$V_{CC} - 0.8$			V
$V_{OL}$	Low-Level Output Voltage	$I_{OL} = 1.0 \text{ mA}^{**}$			0.4	V
$V_{OH}$	High-Level Output Voltage (OSC <sub>OUT</sub> )	$I_{OH} = -200 \mu A$	$V_{CC} - 0.8$			V
$V_{OL}$	Low-Level Output Voltage (OSC <sub>OUT</sub> )	$I_{OL} = 200 \mu A$			0.4	V
$I_{OL}$	Open Drain Output Current ( $\phi_P$ )	$V_{CC} = 5.0V, V_{OL} = 0.4V$	1.0			mA
$I_{OH}$	Open Drain Output Current ( $\phi_P$ )	$V_{OH} = 5.5V$			100	$\mu A$
$R_{ON}$	Analog Switch ON Resistance (2315)			100		$\Omega$
$t_{CS}$	Data to Clock Set Up Time	See Data Input Timing	50			ns
$t_{CH}$	Data to Clock Hold Time	See Data Input Timing	10			ns
$t_{CWH}$	Clock Pulse Width High	See Data Input Timing	50			ns
$t_{CWL}$	Clock Pulse Width Low	See Data Input Timing	50			ns
$t_{ES}$	Clock to Enable Set Up Time	See Data Input Timing	50			ns
$t_{EW}$	Enable Pulse Width	See Data Input Timing	50			ns

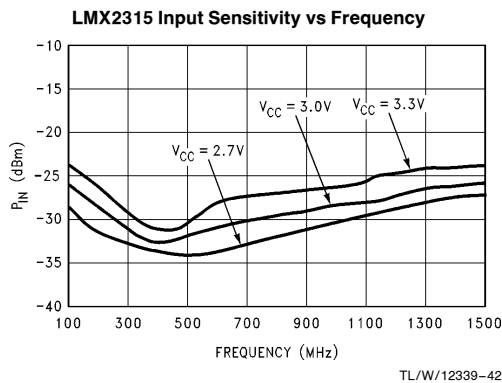
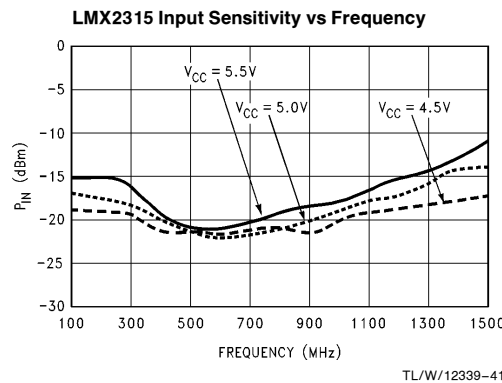
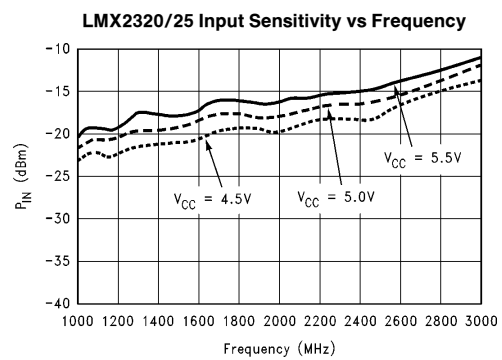
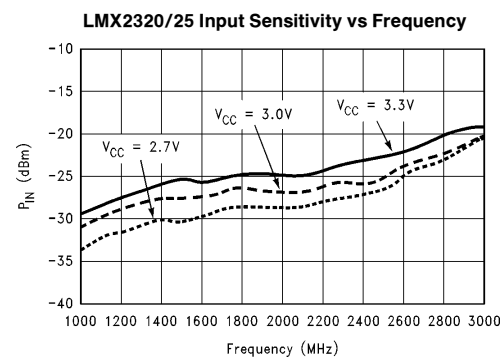
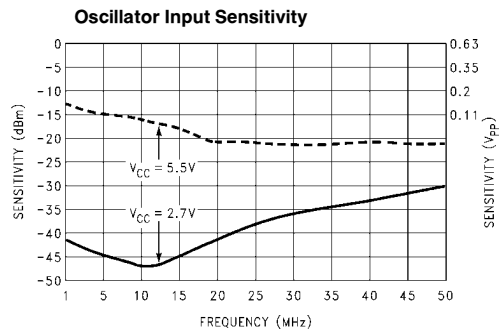
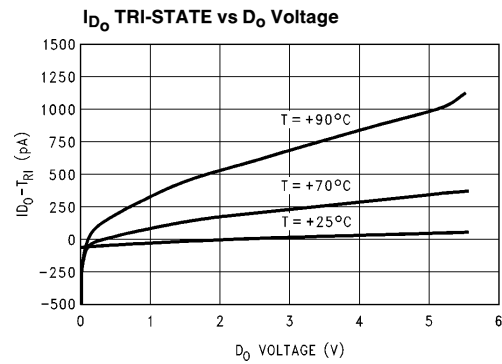
\*\*Except OSC<sub>OUT</sub>

Notes 1, 2, 3: See related equations in Charge Pump Current Specification Definitions

## Typical Performance Characteristics

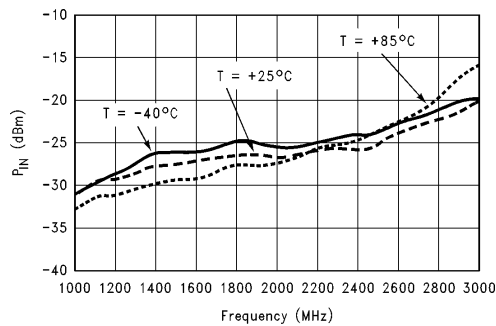


## Typical Performance Characteristics (Continued)



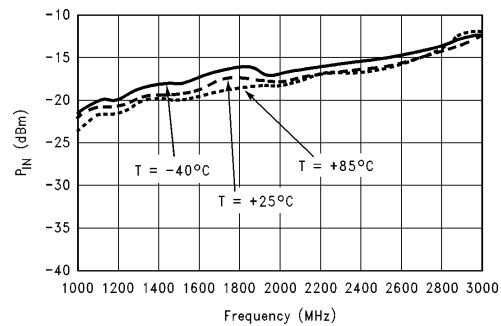
## Typical Performance Characteristics (Continued)

**LMX2320/25 Input Sensitivity at Temperature Variation,  $V_{CC} = 3V$**



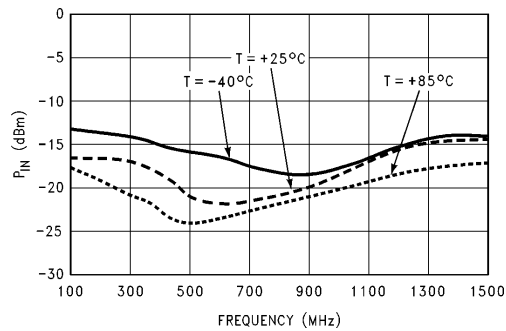
TL/W/12339-12

**LMX2320/25 Input Sensitivity at Temperature Variation,  $V_{CC} = 5V$**



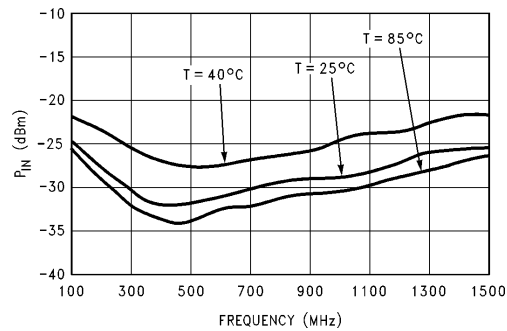
TL/W/12339-13

**LMX2315 Input Sensitivity at Temperature Variation,  $V_{CC} = 5V$**



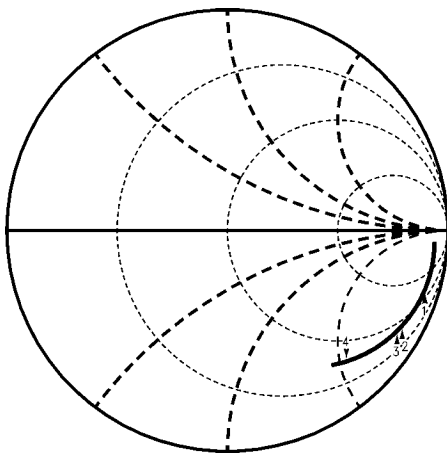
TL/W/12339-43

**LMX2315 Input Sensitivity at Temperature Variation,  $V_{CC} = 3V$**



TL/W/12339-44

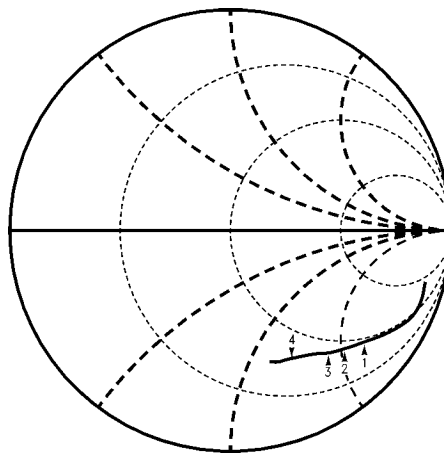
**LMX2315 Input Impedance vs Frequency**  
 $V_{CC} = 2.7V$  to  $5.5V$ ,  $f_{IN} = 100$  MHz to 1,600 MHz



TL/W/12339-45

Marker 1 = 500 MHz, Real = 69, Imag. = -330  
Marker 2 = 900 MHz, Real = 36, Imag. = -193  
Marker 3 = 1 GHz, Real = 35, Imag. = -172  
Marker 4 = 1,500 MHz, Real = 30, Imag. = -106

**LMX2320/25 Input Impedance vs Frequency**  
 $V_{CC} = 2.7V$  to  $5.5V$ ,  $f_{IN} = 500$  MHz to 3000 MHz

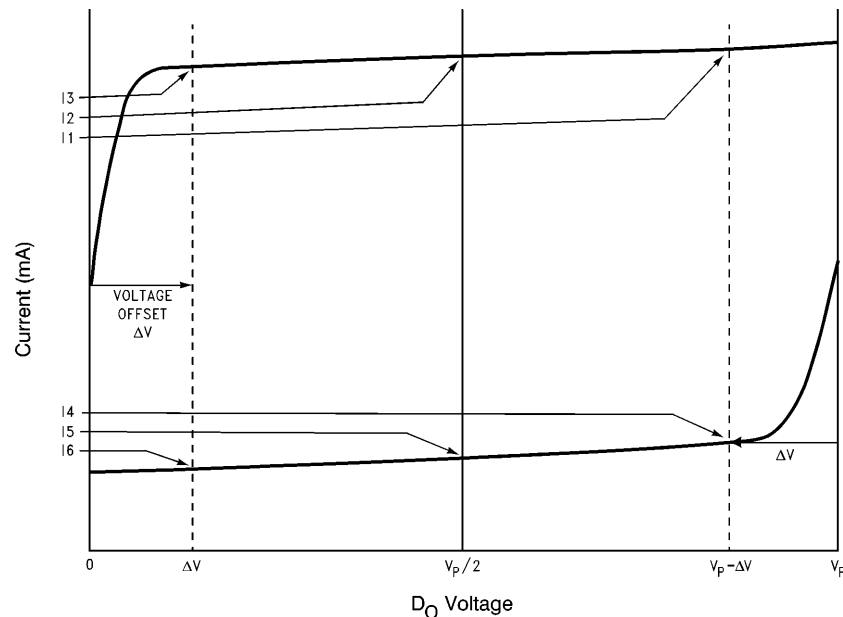


TL/W/12339-15

1 = 1.5 GHz, Real = 48, Im = -128  
2 = 1.8 GHz, Real = 44, Im = -102  
3 = 2.0 GHz, Real = 42, Im = -90  
4 = 2.5 GHz, Real = 36, Im = -72



## Charge Pump Current Specification Definitions



TL/W/12339-16

I1 = CP sink current at  $V_{D_O} = V_P - \Delta V$

I4 = CP source current at  $V_{D_O} = V_P - \Delta V$

I2 = CP sink current at  $V_{D_O} = V_P/2$

I5 = CP source current at  $V_{D_O} = V_P/2$

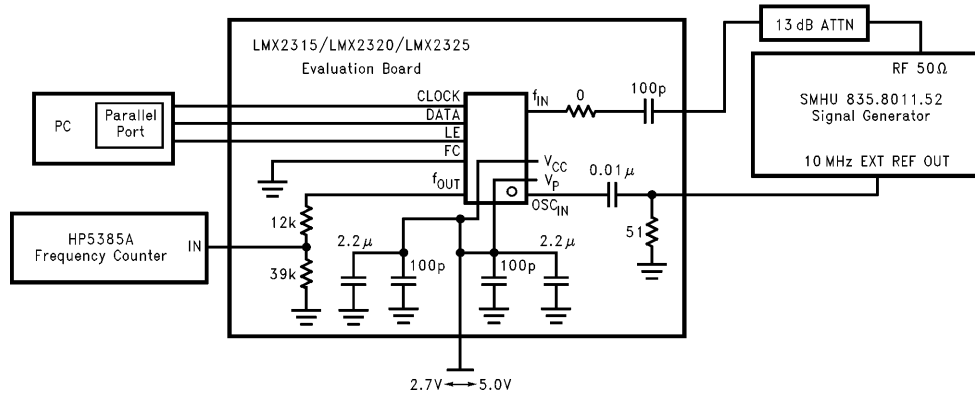
I3 = CP sink current at  $V_{D_O} = \Delta V$

I6 = CP source current at  $V_{D_O} = \Delta V$

$\Delta V$  = Voltage offset from positive and negative rails. Dependent on VCO tuning range relative to  $V_{CC}$  and ground. Typical values are between 0.5V and 1.0V.

1.  $I_{D_O}$  vs  $V_{D_O}$  = Charge Pump Output Current magnitude variation vs Voltage =  $\frac{1}{2} * \frac{|I1| - |I3|}{\frac{1}{2} * (|I1| + |I3|)} * 100\%$  and  $\frac{1}{2} * \frac{|I4| - |I6|}{\frac{1}{2} * (|I4| + |I6|)} * 100\%$
2.  $I_{D_O-sink}$  vs  $I_{D_O-source}$  = Charge Pump Output Current Sink vs Source Mismatch =  $\frac{|I2| - |I5|}{\frac{1}{2} * (|I2| + |I5|)} * 100\%$
3.  $I_{D_O}$  vs  $T_A$  = Charge Pump Output Current magnitude variation vs Temperature =  $\frac{|I2 @ temp| - |I2 @ 25^\circ C|}{|I2 @ 25^\circ C|} * 100\%$  and  $\frac{|I5 @ temp| - |I5 @ 25^\circ C|}{|I5 @ 25^\circ C|} * 100\%$
4.  $K\phi$  = Phase detector/charge pump gain constant =  $\frac{1}{2} * (|I2| + |I5|)$

## RF Sensitivity Test Block Diagram



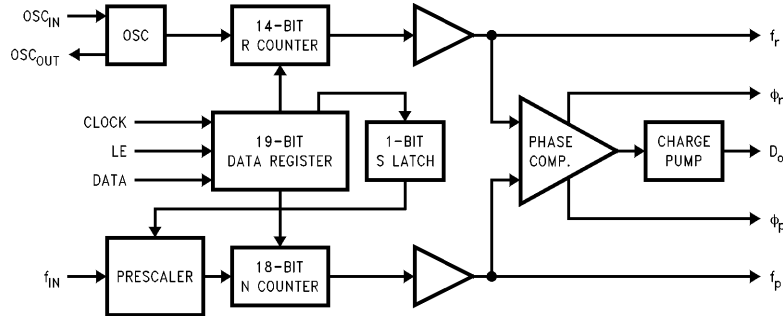
TL/W/12339-17

Note 1: N = 10,000 R = 50 P = 64

Note 2: Sensitivity limit is reached when the error of the divided RF output,  $f_{OUT}$ , is greater than or equal to 1 Hz.

## Functional Description

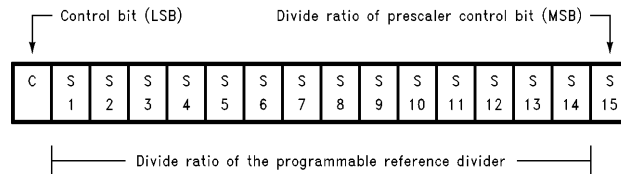
The simplified block diagram below shows the 19-bit data register, the 14-bit R Counter and the S Latch, and the 18-bit N Counter (intermediate latches are not shown). The data stream is clocked (on the rising edge) into the DATA input, MSB first. If the Control Bit (last bit shifted into the R Counter) is HIGH, the DATA is transferred into the R Counter (programmable reference divider) and the S Latch (prescaler select: LMX2315 and LMX2320: 64/65 or 128/129; LMX2325 32/33 or 64/65). If the Control Bit (LSB) is LOW, the DATA is transferred into the N Counter (programmable divider).



TL/W/12339-18

### PROGRAMMABLE REFERENCE DIVIDER (R COUNTER) AND PRESCALER SELECT (S LATCH)

If the Control Bit (last bit shifted into the Data Register) is HIGH, data is transferred from the 19-bit shift register into a 14-bit latch (which sets the 14-bit R Counter) and the 1-bit S Latch (S15, which sets the prescaler: 64/65 or 128/129 for the LMX2315/20 or 32/33 or 64/65 for the LMX2325). Serial data format is shown below.



TL/W/12339-6

### 14-BIT PROGRAMMABLE REFERENCE DIVIDER RATIO (R COUNTER)

Divide Ratio R	S14	S13	S12	S11	S10	S9	S8	S7	S6	S5	S4	S3	S2	S1
3	0	0	0	0	0	0	0	0	0	0	0	0	1	1
4	0	0	0	0	0	0	0	0	0	0	0	1	0	0
•	•	•	•	•	•	•	•	•	•	•	•	•	•	•
16383	1	1	1	1	1	1	1	1	1	1	1	1	1	1

Prescaler Select		S15
LMX2315/20	LMX2325	
128/129	64/65	0
64/65	32/33	1

**Notes:** Divide ratios less than 3 are prohibited.

Divide ratio: 3 to 16383

S1 to S14: These bits select the divide ratio of the programmable reference divider.

C: Control bit (set to HIGH level to load R counter and S Latch)

Data is shifted in MSB first.

### PROGRAMMABLE DIVIDER (N COUNTER)

Figure 10-1 shows the bit fields for the 18-bit SWALLOW register. The register is divided into a 1-bit control field (C) and an 18-bit data field (S0-S17). The control bit (LSB) is bit C. The MSB is bit S17. The register is divided into two sections: 'Divide ratio of swallow counter' (bits C to S10) and 'Divide ratio of programmable counter' (bits S11 to S17).

TI /W/12339-20

**Note:** S8 to S18: Programmable counter divide ratio control bits (3 to 2047)

Divide Ratio A	S 7	S 6	S 5	S 4	S 3	S 2	S 1
0	0	0	0	0	0	0	0
1	0	0	0	0	0	0	1
•	•	•	•	•	•	•	•
127	1	1	1	1	1	1	1

[illegible]

## PULSE SWALLOW FUNCTION

$$f_{VCO} = [(P \times B) + A] \times f_{OSC}/R$$

$f_{VCO}$ : Output frequency of external voltage controlled oscillator (VCO)

B: Preset divide ratio of binary 11-bit programmable counter (3 to 2047)

A: Preset divide ratio of binary 7-bit swallow counter  
( $0 \leq A \leq 127$ ,  $A \leq B$ )

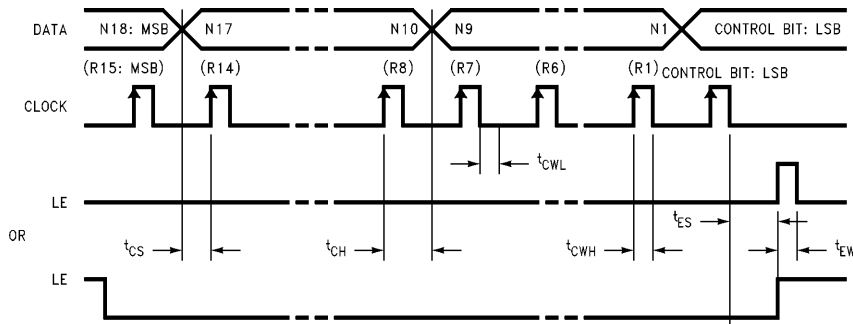
$f_{OSC}$ : Output frequency of the external reference frequency oscillator

R: Preset divide ratio of binary 14-bit programmable reference counter (3 to 16383)

P: Preset modulus of dual modulus prescaler (64 or 128 for 2315/20 or 32 or 64 for 2325)

## Functional Description (Continued)

### SERIAL DATA INPUT TIMING



TL/W/12339-21

**Notes:** Parenthesis data indicates programmable reference divider data.

Data shifted into register on clock rising edge.

Data is shifted in MSB first.

**Test Conditions:** The Serial Data Input Timing is tested using a symmetrical waveform around  $V_{CC}/2$ . The test waveform has an edge rate of 0.6 V/ns with amplitudes of 2.2V @  $V_{CC} = 2.7V$  and 2.6V @  $V_{CC} = 5.5V$ .

### Phase Characteristics

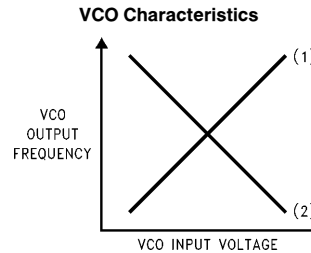
In normal operation, the FC pin is used to reverse the polarity of the phase detector. Both the internal and any external charge pump are affected.

Depending upon VCO characteristics, FC pin should be set accordingly:

When VCO characteristics are like (1), FC should be set HIGH or OPEN CIRCUIT;

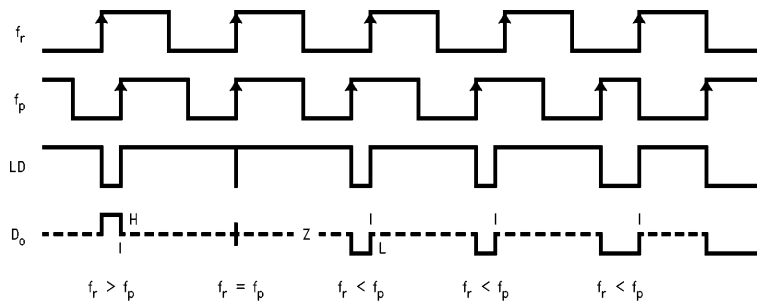
When VCO characteristics are like (2), FC should be set LOW.

When FC is set HIGH or OPEN CIRCUIT, the monitor pin of the phase comparator input,  $f_{out}$ , is set to the reference divider output,  $f_r$ . When FC is set LOW,  $f_{out}$  is set to the programmable divider output,  $f_p$ .



TL/W/12339-22

### PHASE COMPARATOR AND INTERNAL CHARGE PUMP CHARACTERISTICS



TL/W/12339-23

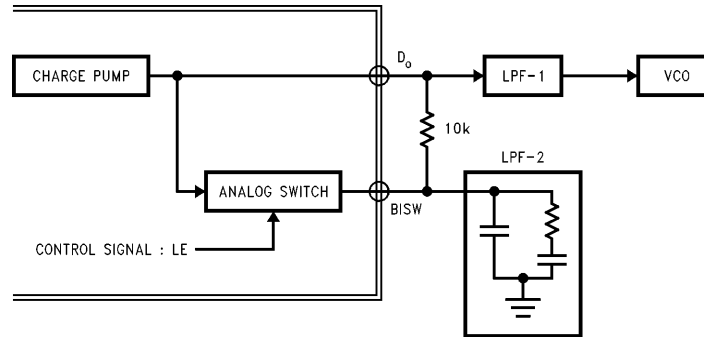
**Notes:** Phase difference detection range:  $-2\pi$  to  $+2\pi$

The minimum width pump up and pump down current pulses occur at the  $D_0$  pin when the loop is locked.

FC = HIGH

## Analog Switch

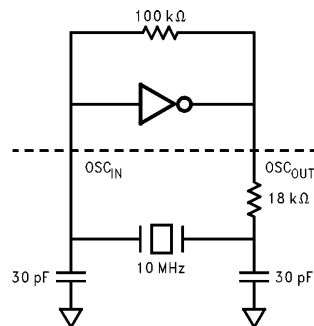
The analog switch is useful for radio systems that utilize a frequency scanning mode and a narrow band mode. The purpose of the analog switch is to decrease the loop filter time constant, allowing the VCO to adjust to its new frequency in a shorter amount of time. This is achieved by adding another filter stage in parallel. The output of the charge pump is normally through the  $D_o$  pin, but when LE is set HIGH, the charge pump output also becomes available at BISW. A typical circuit is shown below. The second filter stage (LPF-2) is effective only when the switch is closed (in the scanning mode).



TL/W/12339-24

## Typical Crystal Oscillator Circuit

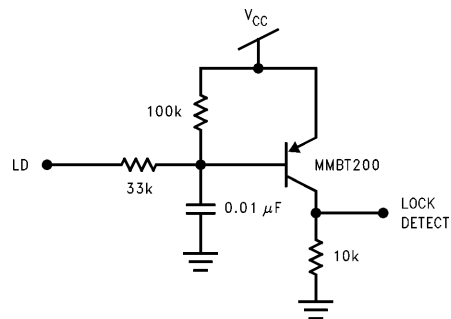
A typical circuit which can be used to implement a crystal oscillator is shown below.



TL/W/12339-52

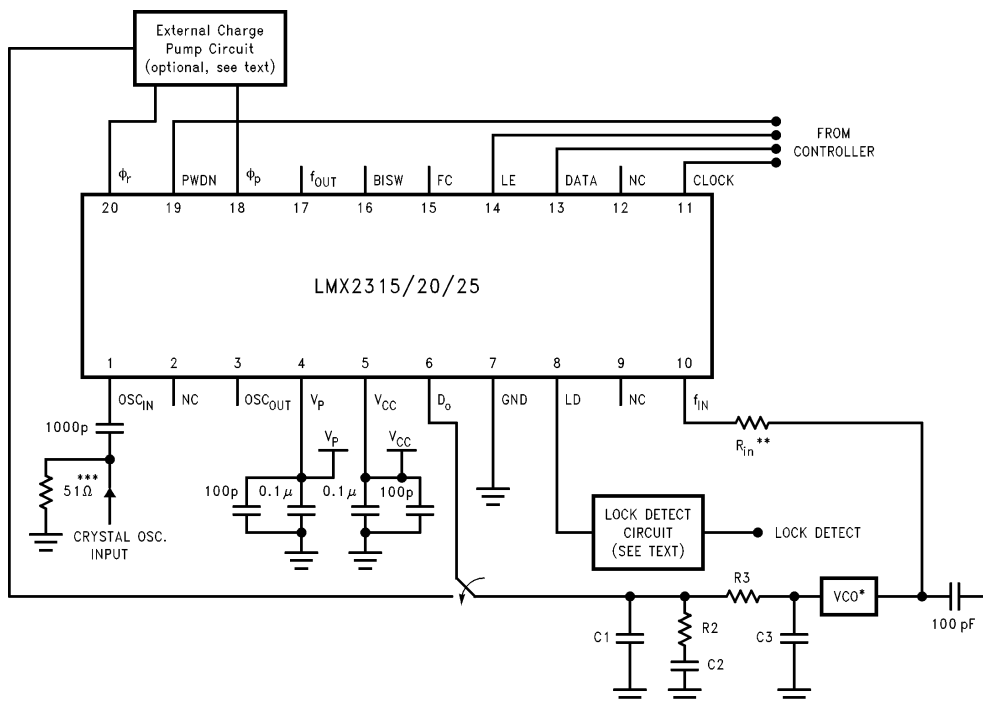
## Typical Lock Detect Circuit

A lock detect circuit is needed in order to provide a steady LOW signal when the PLL is in the locked state. A typical circuit is shown below.



TL/W/12339-26

## Typical Application Example

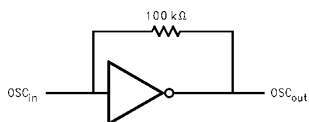


**Operational Notes:**

- \* VCO is assumed AC coupled.

\*\*  $R_{IN}$  increases impedance so that VCO output power is provided to the load rather than the PLL. Typical values are  $10\Omega$  to  $200\Omega$  depending on the VCO power level.  $f_{IN}$  RF impedance ranges from  $40\Omega$  to  $100\Omega$ .

\*\*\* 50 $\Omega$  termination is often used on test boards to allow use of external reference oscillator. For most typical products a CMOS clock is used and no terminating resistor is required. OSC<sub>N</sub> may be AC or DC coupled. AC coupling is recommended because the input circuit provides its own bias. (See *Figure* below)



**Layout Hints:**

Proper use of grounds and bypass capacitors is essential to achieve a high level of performance.

Crosstalk between pins can be reduced by careful board layout.

This is a static sensitive device. It should be handled only at static free work stations.

## Application Information

### LOOP FILTER DESIGN

A block diagram of the basic phase locked loop is shown.

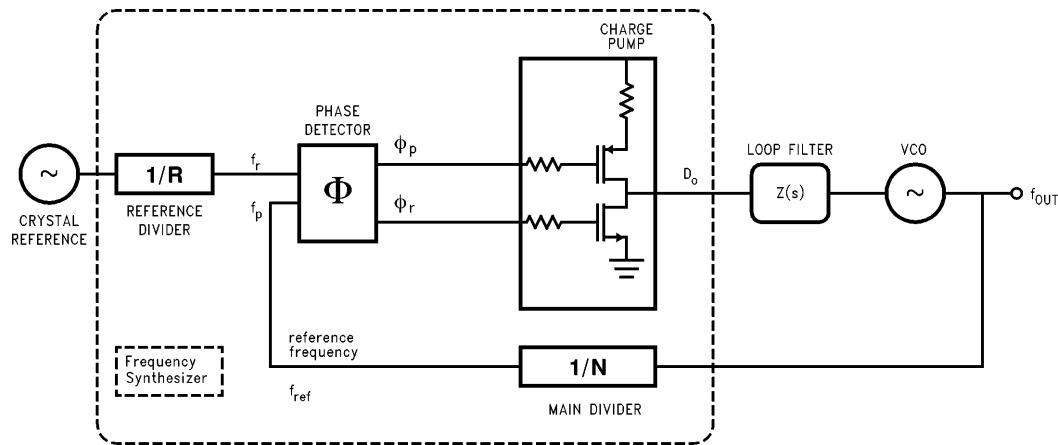
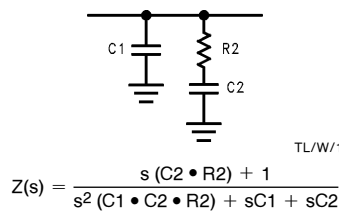


FIGURE 1. Basic Charge Pump Phase Locked Loop

TL/W/12339-29

An example of a passive loop filter configuration, including the transfer function of the loop filter, is shown in Figure 2.



TL/W/12339-30

FIGURE 2. 2nd Order Passive Filter

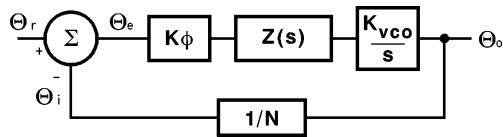
Define the time constants which determine the pole and zero frequencies of the filter transfer function by letting

$$T2 = R2 \cdot C2 \quad (1a)$$

and

$$T1 = R2 \cdot \frac{C1 \cdot C2}{C1 + C2} \quad (1b)$$

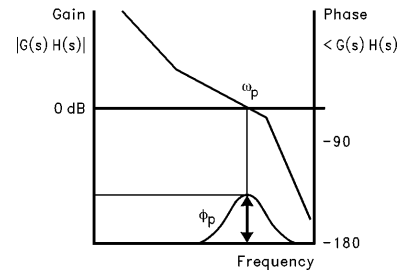
The PLL linear model control circuit is shown along with the open loop transfer function in Figure 3. Using the phase detector and VCO gain constants  $[K\phi]$  and  $K_{VCO}$  and the loop filter transfer function  $[Z(s)]$ , the open loop Bode plot can be calculated. The loop bandwidth is shown on the Bode plot ( $\omega_p$ ) as the point of unity gain. The phase margin is shown to be the difference between the phase at the unity gain point and  $-180^\circ$ .



TL/W/12339-32

$$\begin{aligned} \text{Open Loop Gain} &= \theta_i / \theta_e = H(s) G(s) \\ &= K\phi Z(s) K_{VCO} / Ns \end{aligned}$$

$$\text{Closed Loop Gain} = \theta_o / \theta_i = G(s) / [1 + H(s) G(s)]$$



TL/W/12339-31

FIGURE 3. Open Loop Transfer Function

Thus we can calculate the 3rd order PLL Open Loop Gain in terms of frequency

$$G(s) \cdot H(s) \big|_s = j \cdot \omega = \frac{-K\phi \cdot K_{VCO} (1 + j\omega \cdot T2) \cdot T1}{\omega^2 C1 \cdot N (1 + j\omega \cdot T1)} \cdot \frac{T1}{T2} \quad (2)$$

From equation 2 we can see that the phase term will be dependent on the single pole and zero such that

$$\phi(\omega) = \tan^{-1}(\omega \cdot T2) - \tan^{-1}(\omega \cdot T1) + 180^\circ \quad (3)$$

By setting

$$\frac{d\phi}{d\omega} = \frac{T2}{1 + (\omega \cdot T2)^2} - \frac{T1}{1 + (\omega \cdot T1)^2} = 0 \quad (4)$$

we find the frequency point corresponding to the phase inflection point in terms of the filter time constants T1 and T2. This relationship is given in equation 5.

$$\omega_p = 1 / \sqrt{T2 \cdot T1} \quad (5)$$

For the loop to be stable the unity gain point must occur before the phase reaches  $-180$  degrees. We therefore want the phase margin to be at a maximum when the magnitude of the open loop gain equals 1. Equation 2 then gives

$$C1 = \frac{K\phi \cdot K_{VCO} \cdot T1}{\omega_p^2 \cdot N \cdot T2} \left\| \frac{(1 + j\omega_p \cdot T2)}{(1 + j\omega_p \cdot T1)} \right\| \quad (6)$$

## Application Information (Continued)

Therefore, if we specify the loop bandwidth,  $\omega_p$ , and the phase margin,  $\phi_p$ , Equations 1 through 6 allow us to calculate the two time constants, T1 and T2, as shown in equations 7 and 8. A common rule of thumb is to begin your design with a 45° phase margin.

$$T1 = \frac{\sec\phi_p - \tan\phi_p}{\omega_p} \quad (7)$$

$$T2 = \frac{1}{\omega_p^2 \cdot T1} \quad (8)$$

From the time constants T1, and T2, and the loop bandwidth,  $\omega_p$ , the values for C1, R2, and C2 are obtained in equations 9 to 11.

$$C1 = \frac{T1}{T2} \cdot \frac{K\phi \cdot K_{VCO}}{\omega_p^2 \cdot N} \sqrt{\frac{1 + (\omega_p \cdot T2)^2}{1 + (\omega_p \cdot T1)^2}} \quad (9)$$

$$C2 = C1 \cdot \left( \frac{T2}{T1} - 1 \right) \quad (10)$$

$$R2 = \frac{T2}{C2} \quad (11)$$

$K_{VCO}$ (MHz/V)	Voltage Controlled Oscillator (VCO) Tuning Voltage constant. The frequency vs voltage tuning ratio.
$K\phi$ (mA)	Phase detector/charge pump gain constant. The ratio of the current output to the input phase differential.
N	Main divider ratio. Equal to $RF_{opt}/f_{ref}$
$RF_{opt}$ (MHz)	Radio Frequency output of the VCO at which the loop filter is optimized.
$f_{ref}$ (kHz)	Frequency of the phase detector inputs. Usually equivalent to the RF channel spacing.

In choosing the loop filter components a trade off must be made between lock time, noise, stability, and reference spurs. The greater the loop bandwidth the faster the lock time will be, but a large loop bandwidth could result in higher reference spurs. Wider loop bandwidths generally improve close in phase noise but may increase integrated phase noise depending on the reference input, VCO and division ratios used. The reference spurs can be reduced by reducing the loop bandwidth or by adding more low pass filter stages but the lock time will increase and stability will decrease as a result.

### THIRD ORDER FILTER

A low pass filter section may be needed for some applications that require additional rejection of the reference sidebands, or spurs. This configuration is given in *Figure 4*. In order to compensate for the added low pass section, the component values are recalculated using the new open loop unity gain frequency. The degradation of phase margin caused by the added low pass is then mitigated by slightly increasing C1 and C2 while slightly decreasing R2.

The added attenuation from the low pass filter is:

$$ATTEN = 20 \log[(2\pi f_{ref} \cdot R3 \cdot C3)^2 + 1] \quad (12)$$

Defining the additional time constant as

$$T3 = R3 \cdot C3 \quad (13)$$

Then in terms of the attenuation of the reference spurs added by the low pass pole we have

$$T3 = \sqrt{\frac{10^{ATTEN/20} - 1}{(2\pi \cdot f_{ref})^2}} \quad (14)$$

We then use the calculated value for loop bandwidth  $\omega_c$  in equation 11, to determine the loop filter component values in equations 15–17.  $\omega_c$  is slightly less than  $\omega_p$ , therefore the frequency jump lock time will increase.

$$T2 = \frac{1}{\omega_c^2 \cdot (T1 + T3)} \quad (15)$$

$$\omega_c = \frac{\tan\phi \cdot (T1 + T3)}{[(T1 + T3)^2 + T1 \cdot T3]} \cdot \left[ \sqrt{1 + \frac{(T1 + T3)^2 + T1 \cdot T3}{[\tan\phi \cdot (T1 + T3)]^2}} - 1 \right] \quad (16)$$

$$C1 = \frac{T1}{T2} \cdot \frac{K\phi \cdot K_{VCO}}{\omega_c^2 \cdot N} \cdot \left[ \frac{(1 + \omega_c^2 \cdot T2^2)}{(1 + \omega_c^2 \cdot T1^2)(1 + \omega_c^2 \cdot T3^2)} \right]^{1/2} \quad (17)$$



## Application Information (Continued)

Consider the following application examples:

### Example #1

$$K_{VCO} = 20 \text{ MHz/V}$$

$$K_{\phi} = 5 \text{ mA (Note 1)}$$

$$RF_{opt} = 900 \text{ MHz}$$

$$F_{ref} = 200 \text{ kHz}$$

$$N = RF_{opt}/f_{ref} = 4500$$

$$\omega_p = 2\pi \cdot 20 \text{ kHz} = 1.256e5$$

$$\phi_p = 45^\circ$$

$$ATTEN = 20 \text{ dB}$$

$$T1 = \frac{\sec\phi_p - \tan\phi_p}{\omega_p} = 3.29e-6$$

$$T3 = \sqrt{\frac{10(20/20) - 1}{(2\pi \cdot 200e3)^2}} = 2.387e-6$$

$$\omega_c = \frac{(3.29e-6 + 2.387e-6)}{[(3.29e-6 + 2.387e-6)^2 + 3.29e-6 \cdot 2.387e-6]} \cdot \left[ \sqrt{1 + \frac{(3.29e-6 + 2.387e-6)^2 + 3.29e-6 \cdot 2.387e-6}{[(3.29e-6 + 2.387e-6)]^2}} - 1 \right]$$

$$= 7.045e4$$

$$T2 = \frac{1}{(7.045e4)^2 \cdot (3.29e-6 + 2.387e-6)} = 3.549e-5$$

$$C1 = \frac{3.29e-6}{3.549e-5} \cdot \frac{(5e-3) \cdot 20e6}{(7.045e4)^2 \cdot 4500} \cdot \left[ \frac{[1 + (7.045e4)^2 \cdot (3.549e-5)^2]}{[1 + (7.045e4)^2 \cdot (3.29e-6)^2] [1 + (7.045e4)^2 \cdot (2.387e-6)^2]} \right]^{1/2}$$

$$= 1.085 \text{ nF}$$

$$C2 = 1.085 \text{ nF} \cdot \left( \frac{3.55e-5}{3.29e-6} - 1 \right) = 10.6 \text{ nF};$$

$$R2 = \frac{3.55e-5}{10.6e-9} = 3.35 \text{ k}\Omega;$$

$$\text{if we choose } R3 = 22\text{k}; \text{ then } C3 = \frac{2.34e-6}{22e3} = 106 \text{ pF.}$$

Converting to standard component values gives the following filter values, which are shown in *Figure 4*.

$$C1 = 1000 \text{ pF}$$

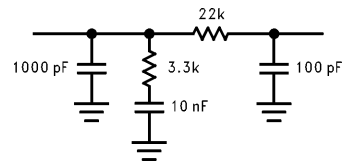
$$R2 = 3.3 \text{ k}\Omega$$

$$C2 = 10 \text{ nF}$$

$$R3 = 22 \text{ k}\Omega$$

$$C3 = 100 \text{ pF}$$

**Note 1:** See related equation for  $K_{\phi}$  in Charge Pump Current Specification Definitions. For this example  $V_p = 5.0\text{V}$ . The value of  $K_{\phi}$  can then be approximated using the curves in the Typical Performance Characteristics for Charge Pump Current vs.  $D_o$  Voltage. The units for  $K_{\phi}$  are in mA. You may also use  $K_{\phi} = (5 \text{ mA}/2\pi \text{ rad})$ , but in this case you must convert  $K_{VCO}$  to (rad/V) multiplying by  $2\pi$ .

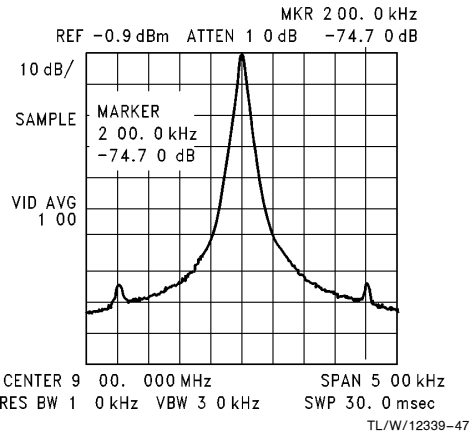


TL/W/12339-46

**FIGURE 4. ~ 20 kHz Loop Filter**

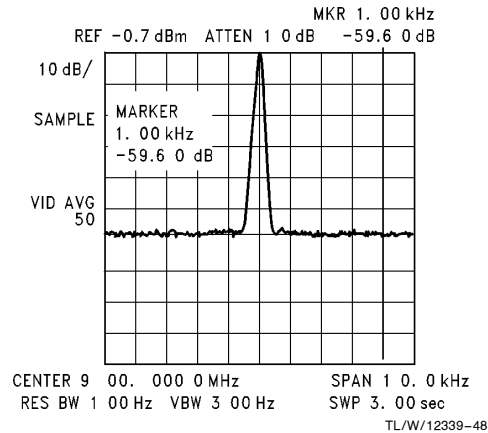
## Application Information (Continued)

### MEASUREMENT RESULTS (Example #1)



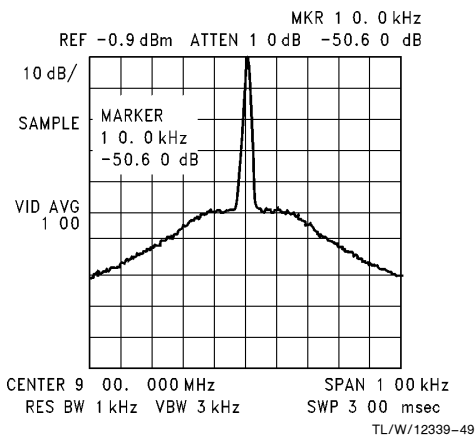
**FIGURE 5. PLL Reference Spurs**

The reference spurious level is  $< -74$  dBc, due to the loop filter attenuation and the low spurious noise level of the LMX2315.



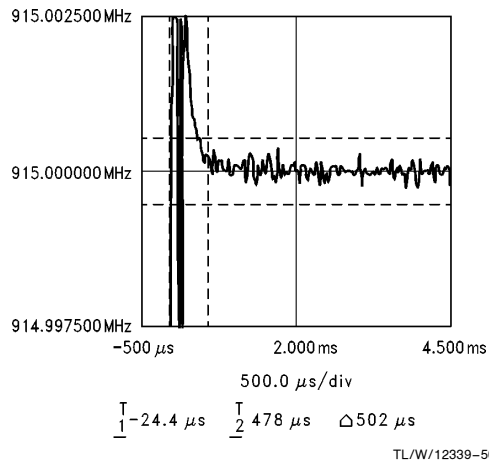
**FIGURE 7. PLL Phase Noise @ 1 kHz Offset**

The phase noise level at 1 kHz offset is  $-79.5$  dBc/Hz.



**FIGURE 6. PLL Phase Noise 10 kHz Offset**

The phase noise level at 10 kHz offset is  $-80$  dBc/Hz.



**FIGURE 8. Frequency Jump Lock Time**

Of concern in any PLL loop filter design is the time it takes to lock in to a new frequency when switching channels. *Figure 8* shows the switching waveforms for a frequency jump of 865 MHz to 915 MHz. By narrowing the frequency span of the HP53310A Modulation Domain Analyzer enables evaluation of the frequency lock time to within  $\pm 500$  Hz. The lock time is seen to be less than 500  $\mu$ s for a frequency jump of 50 MHz.

## Application Information (Continued)

### Example #2

$$K_{VCO} = 34 \text{ MHz/V}$$

$$K_{\phi} = 2.8 \text{ mA (Note 1)}$$

$$RF_{opt} = 1665 \text{ MHz}$$

$$F_{ref} = 300 \text{ kHz}$$

$$N = RF_{opt}/f_{ref} = 5550$$

$$\omega_p = 2\pi \cdot 20 \text{ kHz} = 1.256e5$$

$$\phi_p = 43$$

$$ATTEN = 12 \text{ dB}$$

$$T1 = \frac{\sec\phi - \tan\phi}{\omega_p} = 3.462e-6$$

$$T3 = \sqrt{\frac{10(12/20) - 1}{(2\pi \cdot 300e3)^2}} = 9.16e-7$$

$$\omega_c = \frac{\tan 43 (3.862e-6 + 9.16e-7)}{(3.462e-6 + 9.16e-7)^2 + 3.462e-6 \cdot 9.16e-7} \cdot \left[ \sqrt{1 + \frac{(3.462e-6 + 9.16e-7)^2 + 3.462e-6 \cdot 9.16e-7}{[\tan 43 (3.462e-6 + 9.16e-7)]^2}} - 1 \right]$$

$$T2 = \frac{1}{(9.682e4)^2 (3.462e-6 + 9.16e-7)} = 2.437e-5$$

$$C1 = \frac{3.462e-6 (2.8e-3) \cdot 34e6}{2.437e-5 (9.682e4)^2 \cdot 5550} \cdot \left[ \frac{[1 + (9.682e4)^2 \cdot (2.437e-5)^2]}{[1 + (9.682e4)^2 (3.462e-6)^2] [1 + (9.682e4)^2 \cdot (9.16e-7)^2]} \right]^{1/2}$$

$$= 0.63 \text{ nF}$$

$$C2 = 0.63 \text{ nF} \left( \frac{2.437e-5}{3.402e-6} - 1 \right) = 3.88 \text{ nF};$$

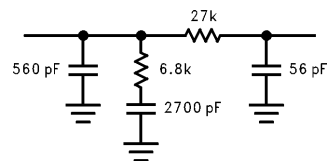
$$R2 = \frac{2.437e-5}{3.88e-9} = 6.28 \text{ k}\Omega;$$

if we choose  $R3 = 27\text{k}$ ; then  $C3 = \frac{9.16e-7}{27e3} = 34 \text{ pF}$ .

Converting to standard component values gives the following filter values, which are shown in *Figure 4*.

- $C1 = 560 \text{ pF}$
- $R2 = 6.8 \text{ k}\Omega$
- $C2 = 2700 \text{ pF}$
- $R3 = 27 \text{ k}\Omega$
- $C3 = 56 \text{ pF}$

**Note 1:** See related equation for  $K_{\phi}$  in Charge Pump Current Specification Definitions. For this example  $V_P = 3.3\text{V}$ . The value for  $K_{\phi}$  can then be approximated using the curves in the Typical Performance Characteristics for Charge Pump Current vs.  $D_O$  Voltage. The units for  $K_{\phi}$  are in mA. You may also use  $K_{\phi} = (2.8 \text{ mA}/2\pi \text{ rad})$ , but in this case you must convert  $K_{VCO}$  to (rad/V) multiplying by  $2\pi$ .

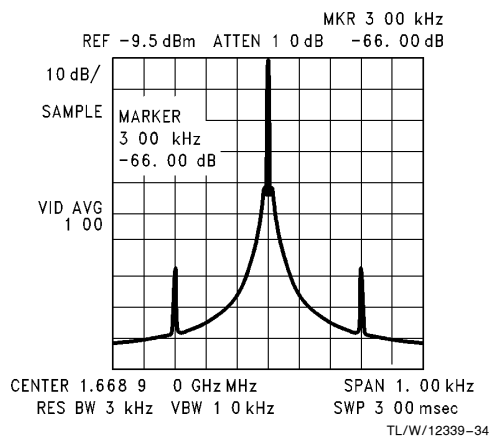


TL/W/12339-33

**FIGURE 9. ~ 20 kHz Loop Filter**

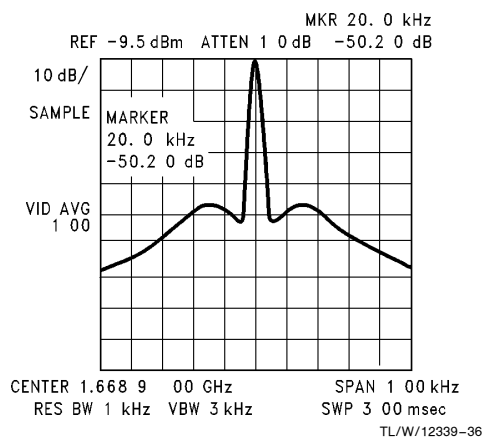
## Application Information (Continued)

### MEASUREMENT RESULTS (Example #2)



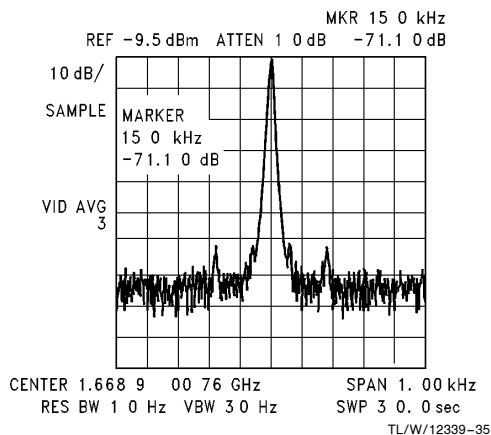
**FIGURE 10. PLL Reference Spurs**

The reference spurious level is  $< -65$  dBc, due to the loop filter attenuation and the low spurious noise level of the LMX2320.



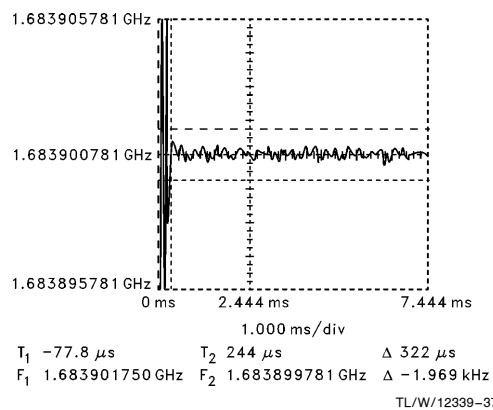
**FIGURE 12. PLL Phase Noise 20 kHz Offset**

The phase noise level at 20 kHz offset is  $-80$  dBc/Hz.



**FIGURE 11. PLL Phase Noise @ 150 Hz Offset**

The phase noise level at 150 Hz offset is  $-81.1$  dBc/Hz. The spurs at 60 and 180 Hz offset are due to 60 Hz line noise from the power supply.



**FIGURE 13. Frequency Jump Lock Time**

Of concern in any PLL loop filter design is the time it takes to lock in to a new frequency when switching channels. Figure 13 shows the switching waveforms for a frequency jump of 1650.9 MHz to 1683.9 MHz. By narrowing the frequency span of the HP53310A Modulation Domain Analyzer enables evaluation of the frequency lock time to within  $\pm 1$  kHz. The lock time is seen to be less than 500  $\mu$ s for a frequency jump of 33 MHz.

## Application Information (Continued)

### EXTERNAL CHARGE PUMP

The LMX PLLatinum series of frequency synthesizers are equipped with an internal balanced charge pump as well as outputs for driving an external charge pump. Although the superior performance of NSC's on board charge pump eliminates the need for an external charge pump in most applications, certain system requirements are more stringent. In these cases, using an external charge pump allows the designer to take direct control of such parameters as charge pump voltage swing, current magnitude, TRI-STATE leakage, and temperature compensation.

One possible architecture for an external charge pump current source is shown in Figure 14. The signals  $\phi_p$  and  $\phi_r$  in the diagram, correspond to the phase detector outputs of the 2315/20/25 frequency synthesizers. These logic signals are converted into current pulses, using the circuitry shown in Figure 14, to enable either charging or discharging of the loop filter components to control the output frequency of the PLL.

Referring to Figure 14, the design goal is to generate a 5 mA current which is relatively constant to within 5V of the power supply rail. To accomplish this, it is important to establish as large of a voltage drop across R5, R8 as possible without saturating Q2, Q4. A voltage of approximately 300 mV provides a good compromise. This allows the current source reference being generated to be relatively repeatable in the absence of good Q1, Q2/Q3, Q4 matching. (Matched transistor pairs is recommended.) The  $\phi_p$  and  $\phi_r$  outputs are rated for a maximum output load current of 1 mA while 5 mA current sources are desired. The voltages developed across R4, 9 will consequently be approximately 258 mV, or 42 mV less than R8, 5, due to the current density differences  $\{0.026 \cdot 1n(5 \text{ mA}/1 \text{ mA})\}$  through the Q1, Q2/Q3, Q4 pairs.

In order to calculate the value of R7 it is necessary to first estimate the forward base to emitter voltage drop ( $V_{fn,p}$ ) of the transistors used, the  $V_{OL}$  drop of  $\phi_p$ , and the  $V_{OH}$  drop of  $\phi_r$ 's under 1 mA loads. ( $\phi_p$ 's  $V_{OL} < 0.1V$  and ( $\phi_r$ 's  $V_{OH} < 0.1V$ ).

Knowing these parameters along with the desired current allow us to design a simple external charge pump. Separating the pump up and pump down circuits facilitates the nodal analysis and give the following equations.

$$R_4 = \frac{V_{R5} - V_T \cdot 1n\left(\frac{i_{source}}{i_{p \max}}\right)}{i_{source}}$$

$$R_9 = \frac{V_{R8} - V_T \cdot 1n\left(\frac{i_{sink}}{i_{n \max}}\right)}{i_{sink}}$$

$$R_5 = \frac{V_{R5} \cdot (\beta_p + 1)}{i_{p \max} \cdot (\beta_p + 1) - i_{source}}$$

$$R_8 = \frac{V_{R8} \cdot (\beta_n + 1)}{i_{r \max} \cdot (\beta_n + 1) - i_{sink}}$$

$$R_6 = \frac{(V_p - V_{VOL\phi p}) - (V_{R5} + V_{fp})}{i_{p \max}}$$

$$R_7 = \frac{(V_p - V_{VOH\phi p}) - (V_{R8} + V_{fn})}{i_{\max}}$$

### EXAMPLE

Typical Device Parameters  $\beta_n = 100, \beta_p = 50$

Typical System Parameters  $V_p = 5.0V;$

$V_{cntl} = 0.5V - 4.5V;$

$V_{\phi p} = 0.0V, V_{\phi r} = 5.0V$

Design Parameters

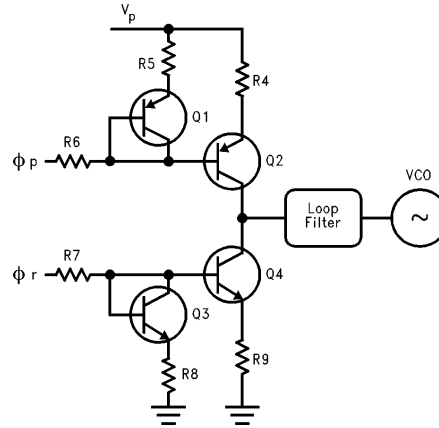
$I_{SINK} = I_{SOURCE} = 5.0 \text{ mA};$

$V_{fn} = V_{fp} = 0.8V$

$I_{r \max} = I_{p \max} = 1 \text{ mA}$

$V_{R8} = V_{R5} = 0.3V$

$V_{OL\phi p} = V_{OH\phi p} = 100 \text{ mV}$



TL/W/12339-39

FIGURE 14

Therefore select

$$R_4 = R_9 = \frac{0.3V - 0.026 \cdot 1n(5.0 \text{ mA}/1.0 \text{ mA})}{5 \text{ mA}} = 51.6\Omega$$

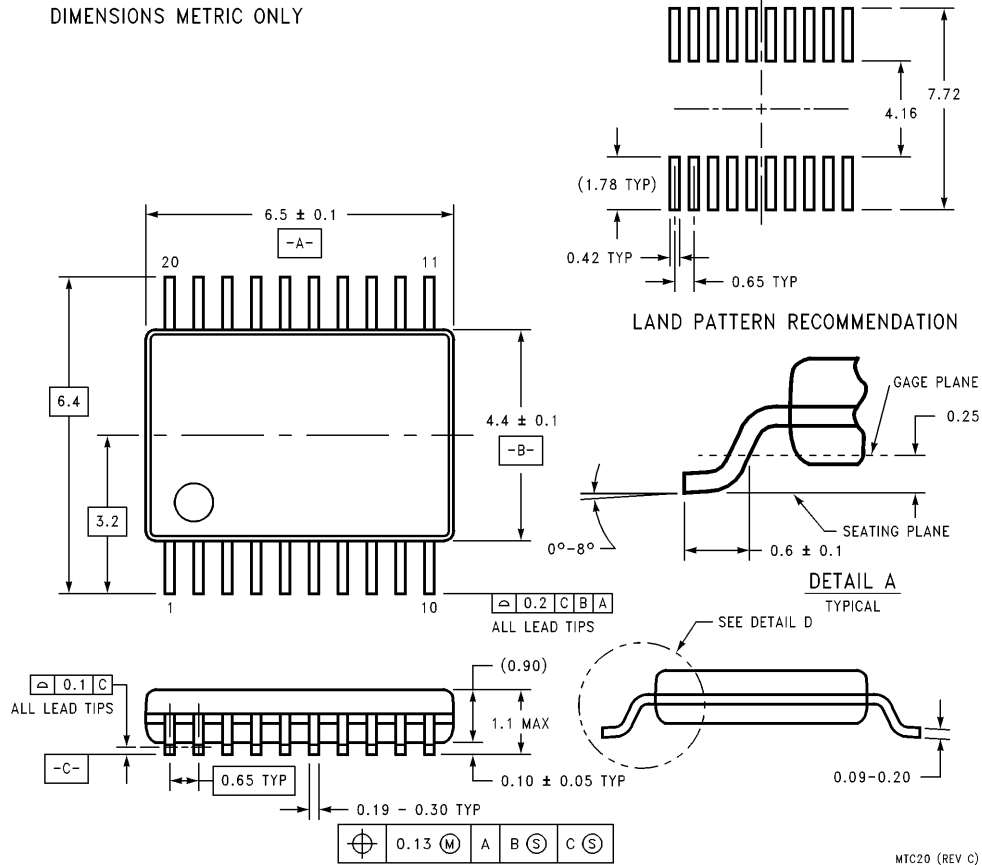
$$R_5 = \frac{0.3V \cdot (50 + 1)}{1.0 \text{ mA} \cdot (50 + 1) - 5.0 \text{ mA}} = 332\Omega$$

$$R_8 = \frac{0.3V \cdot (100 + 1)}{1.0 \text{ mA} \cdot (100 + 1) - 5.0 \text{ mA}} = 315.6\Omega$$

$$R_6 = R_7 = \frac{(5V - 0.1V) - (0.3V + 0.8V)}{1.0 \text{ mA}} = 3.8 \text{ k}\Omega$$

**LMX2315/LMX2320/LMX2325 PLLatinum Frequency  
Synthesizer for RF Personal Communications  
LMX2325 2.5 GHz LMX2320 2.0 GHz LMX2315 1.2 GHz**

**Physical Dimensions** millimeters



**LIFE SUPPORT POLICY**

NATIONAL'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF THE PRESIDENT OF NATIONAL SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform, when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.



**National Semiconductor Corporation**  
1111 West Bardin Road  
Arlington, TX 76017  
Tel: 1(800) 272-9959  
Fax: 1(800) 737-7018

<http://www.national.com>

**National Semiconductor Europe**

Fax: +49 (0) 180-530 85 86  
Email: [europe.support@nsc.com](mailto:europe.support@nsc.com)  
Deutsch Tel: +49 (0) 180-530 85 85  
English Tel: +49 (0) 180-532 78 32  
Français Tel: +49 (0) 180-532 93 58  
Italiano Tel: +49 (0) 180-534 16 80

**National Semiconductor Hong Kong Ltd.**

19th Floor, Straight Block,  
Ocean Centre, 5 Canton Rd.  
Tsimshatsui, Kowloon  
Hong Kong  
Tel: (852) 2737-1600  
Fax: (852) 2736-9960

**National Semiconductor Japan Ltd.**

Tel: 81-043-299-2308  
Fax: 81-043-299-2408

National does not assume any responsibility for use of any circuitry described, no circuit patent licenses are implied and National reserves the right at any time without notice to change said circuitry and specifications.